

isc Silicon PNP Power Transistor
2SB522
DESCRIPTION

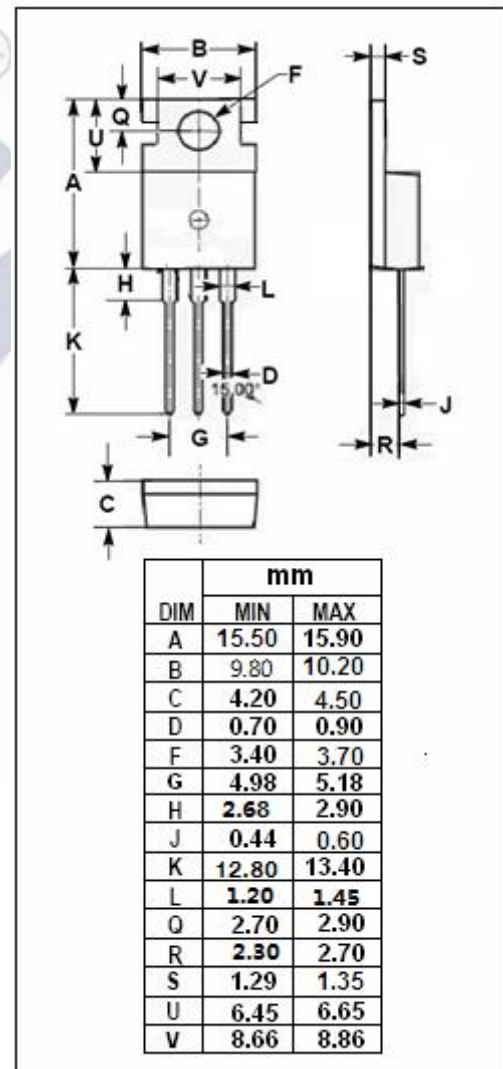
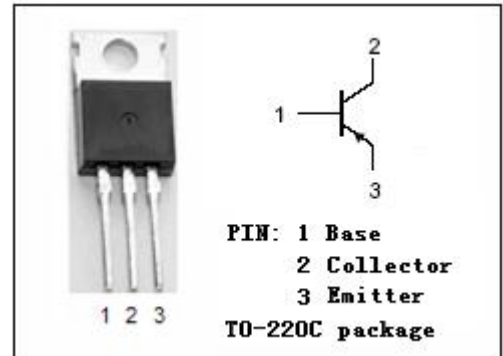
- Collector-Emitter Sustaining Voltage-
: $V_{CE(SUS)} = -60V(\text{Min})$
- Low Collector Saturation Voltage-
: $V_{CE(sat)} = -0.4V(\text{Max.}) @ I_C = -3A$
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

APPLICATIONS

- Designed for high current switching applications.

ABSOLUTE MAXIMUM RATINGS ($T_a = 25^\circ\text{C}$)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	-60	V
V_{CEO}	Collector-Emitter Voltage	-60	V
V_{EBO}	Emitter-Base Voltage	-8	V
I_C	Collector Current-Continuous	-5	A
P_C	Collector Power Dissipation @ $T_c = 25^\circ\text{C}$	25	W
T_J	Junction Temperature	150	$^\circ\text{C}$
T_{stg}	Storage Temperature	-55~150	$^\circ\text{C}$



isc Silicon PNP Power Transistor**2SB522****ELECTRICAL CHARACTERISTICS****T_j=25°C unless otherwise specified**

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{CEO(SUS)}	Collector-Emitter Sustaining Voltage	I _C = -10mA; I _B = 0	-60			V
V _{(BR)EBO}	Emitter-Base Breakdown Voltage	I _E = -1mA; I _C = 0	-8			V
V _{CE(sat)}	Collector-Emitter Saturation Voltage	I _C = -3A; I _B = -0.15A			-0.4	V
V _{BE(sat)}	Base-Emitter Saturation Voltage	I _C = -3A; I _B = -0.15A			-1.2	V
I _{CBO}	Collector Cutoff Current	V _{CB} = -50V; I _E = 0			-100	μ A
I _{EBO}	Emitter Cutoff Current	V _{EB} = -8V; I _C = 0			-10	μ A
h _{FE}	DC Current Gain	I _C = -2.5A; V _{CE} = -2V	50			
f _T	Current-Gain—Bandwidth Product	I _C =-0.2A ; V _{CE} = -5V		7		MHz